DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

METHOD OF FORMING DIFFERENT OXIDE THICKNESS FOR HIGH VOLTAGE TRANSISTOR AND MEMORY CELL TUNNEL DIELECTRIC

		led on (if	applicable).
	ve reviewed and understan as amended by any amendn	d the contents of the above-identified nent referred to above.	ed specification,
I acknowledge the dut 1.56.	y to disclose all informatio	n which is material to patentability	as defined in 37 CFR §
application(s) for pate designated at least one	nt or inventor's certificate, e country other than the Un n for patent or inventor's ce	U.S.C. § 119(a)-(d) or § 365(b) of a or § 365(a) of any PCT Internationa ited States, listed below and have al ertificate having a filing date before	I application which so identified below
Prior Foreign Applica	tion(s)		Priority Claimed Yes No
Number	Country	Day/Month/Year Filed	
Number	Country	Day/Month/Year Filed	
I hereby claim the ben	nefit under 35 U.S.C. § 119	(e) of any United States provisional	application(s) below.
Application Number	Filing Date		
Application Number	Filing Date		

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose all information

Application Number	Filing Date	Status: Patented, Pending, Abandoned
Application Number	Filing Date	Status: Patented, Pending, Abandoned
on information and belief a knowledge that willful fals	are believed to be true e statements and the O1 and that such will	of my own knowledge are true and that all statement; and further that these statements were made with the like so made are punishable by fine or imprisonment ful false statements may jeopardize the validity of the
Full name of sole or first in	nventor <u>Ge</u>	eng-Chuan Chern
Inventor's signature		Date
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Full name of sole or first in Inventor's signature		
		Date